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(54) **SEMICONDUCTOR PACKAGE WITH SEMICONDUCTOR DEVICES**

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(57) **ABSTRACT**

Provided is a semiconductor package including a first semiconductor device including a first semiconductor substrate, a first interconnect structure on the first semiconductor substrate, and a trench extending into the first interconnect structure and a portion of the first semiconductor substrate, a second semiconductor device on the first semiconductor device, and a cover insulating layer on the first semiconductor device and a side surface of the second semiconductor device, the cover insulating layer including a first portion filling the trench included in the first semiconductor device and contacting the first semiconductor substrate.